Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Automotive Dual N-Channel 12 V (D-S) 175 °C MOSFETs

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
V_{DS} (V)	12	12
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0065	0.0033
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0093	0.0045
I_D (A)	20	60
Configuration	Dual N	
Package	PowerPAK® SO-8L Dual Asymmetric	

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified [d]
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

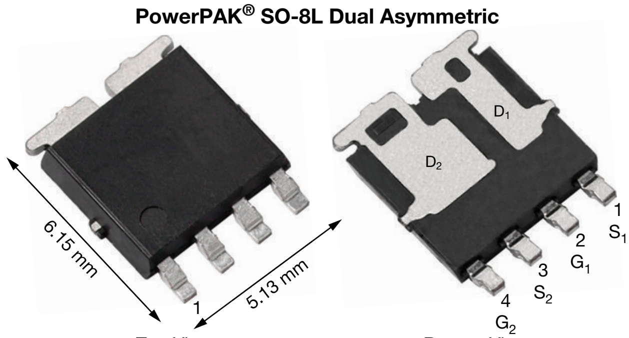
AUTOMOTIVE GRADE

Pb-free

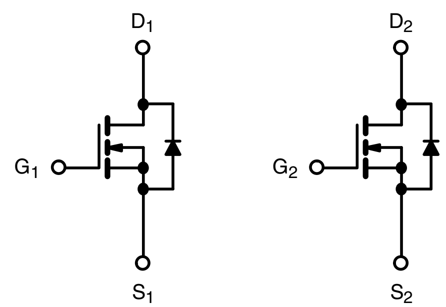
RoHS COMPLIANT

HALOGEN FREE

PowerPAK® SO-8L Dual Asymmetric



Top View   Bottom View



N-Channel 1 MOSFET   N-Channel 2 MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-Source Voltage		V_{DS}	12	12	V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current [a]	T_C = 25 °C	I_D	20	60	A
	T_C = 125 °C		20	60	
Continuous Source Current (Diode Conduction)		I_S	20[a]	44	
Pulsed Drain Current [b]		I_{DM}	80	180	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	18	18	
Single Pulse Avalanche Energy		E_{AS}	16.2	16.2	mJ
Maximum Power Dissipation [b]	T_C = 25 °C	P_D	27	48	W
	T_C = 125 °C		9	16	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175		°C
Soldering Recommendations (Peak Temperature) [e, f]			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-Ambient	PCB Mount [c]	R_{thJA}	85	85	°C/W
Junction-to-Case (Drain)		R_{thJC}	5.5	3.1	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).
d. Parametric verification ongoing.
e. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)								
PARAMETER	**SYMBOL**	**TEST CONDITIONS**			**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static								
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA		N-Ch 1	12	-	-	V
		V_{GS} = 0 V, I_D = 250 μA		N-Ch 2	12	-	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA		N-Ch 1	1	1.5	2	
		V_{DS} = V_{GS}, I_D = 250 μA		N-Ch 2	1	1.5	2	
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		N-Ch 1	-	-	± 100	nA
				N-Ch 2	-	-	± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 12 V	N-Ch 1	-	-	1	μA
		V_{GS} = 0 V	V_{DS} = 12 V	N-Ch 2	-	-	1	
		V_{GS} = 0 V	V_{DS} = 12 V, T_J = 125 °C	N-Ch 1	-	-	50	
		V_{GS} = 0 V	V_{DS} = 12 V, T_J = 125 °C	N-Ch 2	-	-	50	
		V_{GS} = 0 V	V_{DS} = 12 V, T_J = 175 °C	N-Ch 1	-	-	500	
		V_{GS} = 0 V	V_{DS} = 12 V, T_J = 175 °C	N-Ch 2	-	-	500	
On-State Drain Current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	N-Ch 1	20	-	-	A
		V_{GS} = 10 V	V_{DS} ≥ 5 V	N-Ch 2	30	-	-	
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 15 A	N-Ch 1	-	0.0052	0.0065	Ω
		V_{GS} = 10 V	I_D = 20 A	N-Ch 2	-	0.0025	0.0033	
		V_{GS} = 10 V	I_D = 15 A, T_J = 125 °C	N-Ch 1	-	0.0075	-	
		V_{GS} = 10 V	I_D = 20 A, T_J = 125 °C	N-Ch 2	-	0.0031	-	
		V_{GS} = 10 V	I_D = 15 A, T_J = 175 °C	N-Ch 1	-	0.0085	-	
		V_{GS} = 10 V	I_D = 20 A, T_J = 175 °C	N-Ch 2	-	0.0038	-	
		V_{GS} = 4.5 V	I_D = 13 A	N-Ch 1	-	0.0075	0.0093	
		V_{GS} = 4.5 V	I_D = 18 A	N-Ch 2	-	0.0034	0.0045	
Forward Transconductance [b]	g_{fs}	V_{DS} = 10 V, I_D = 15 A		N-Ch 1	-	49	-	S
		V_{DS} = 10 V, I_D = 20 A		N-Ch 2	-	91	-	
Dynamic [b]								
Input Capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 6 V, f = 1 MHz	N-Ch 1	-	777	975	pF
		V_{GS} = 0 V	V_{DS} = 6 V, f = 1 MHz	N-Ch 2	-	2018	2525	
Output Capacitance	C_{oss}	V_{GS} = 0 V	V_{DS} = 6 V, f = 1 MHz	N-Ch 1	-	539	675	
		V_{GS} = 0 V	V_{DS} = 6 V, f = 1 MHz	N-Ch 2	-	1313	1645	
Reverse Transfer Capacitance	C_{rss}	V_{GS} = 0 V	V_{DS} = 6 V, f = 1 MHz	N-Ch 1	-	270	340	
		V_{GS} = 0 V	V_{DS} = 6 V, f = 1 MHz	N-Ch 2	-	683	855	
Total Gate Charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 6 V, I_D = 20 A	N-Ch 1	-	14.5	22	nC
		V_{GS} = 10 V	V_{DS} = 6 V, I_D = 60 A	N-Ch 2	-	35.9	54	
Gate-Source Charge [c]	Q_{gs}	V_{GS} = 10 V	V_{DS} = 6 V, I_D = 20 A	N-Ch 1	-	1.7	-	
		V_{GS} = 10 V	V_{DS} = 6 V, I_D = 60 A	N-Ch 2	-	4.1	-	
Gate-Drain Charge [c]	Q_{gd}	V_{GS} = 10 V	V_{DS} = 6 V, I_D = 20 A	N-Ch 1	-	2.1	-	
		V_{GS} = 10 V	V_{DS} = 6 V, I_D = 60 A	N-Ch 2	-	4.3	-	
Gate Resistance	R_g	f = 1 MHz		N-Ch 1	1.3	2.6	4	Ω
				N-Ch 2	0.5	1.1	1.7	

Notes

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

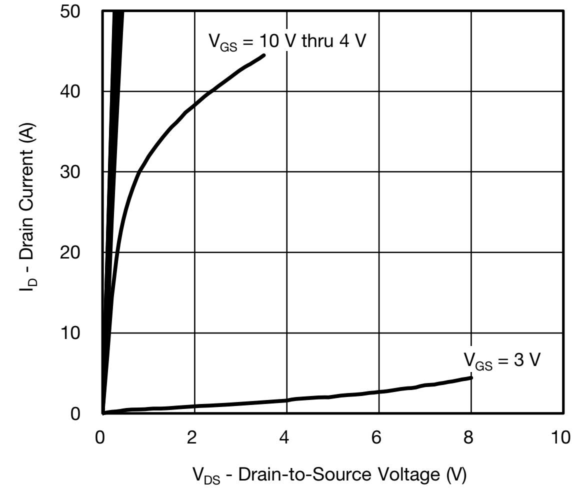
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Turn-On Delay Time [c]	$t_{d(on)}$	V_{DD} = 6 V, R_L = 0.3 Ω $I_D \cong$ 20 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	8.8	13.5	ns
		V_{DD} = 6 V, R_L = 0.1 Ω $I_D \cong$ 60 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	10.7	16.5	
Rise Time [c]	t_r	V_{DD} = 6 V, R_L = 0.3 Ω $I_D \cong$ 20 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	3.2	5	
		V_{DD} = 6 V, R_L = 0.1 Ω $I_D \cong$ 60 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	4.5	7	
Turn-Off Delay Time [c]	$t_{d(off)}$	V_{DD} = 6 V, R_L = 0.3 Ω $I_D \cong$ 20 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	20	30	
		V_{DD} = 6 V, R_L = 0.1 Ω $I_D \cong$ 60 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	28	42	
Fall Time [c]	t_f	V_{DD} = 6 V, R_L = 0.3 Ω $I_D \cong$ 20 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 1	-	2.6	4	
		V_{DD} = 6 V, R_L = 0.1 Ω $I_D \cong$ 60 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch 2	-	5	8	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed Current [a]	I_{SM}		N-Ch 1	-	-	80	A
			N-Ch 2	-	-	180	
Forward Voltage	V_{SD}	I_F = 10 A, V_{GS} = 0 V	N-Ch 1	-	0.8	1.2	V
		I_F = 20 A, V_{GS} = 0 V	N-Ch 2	-	0.8	1.2	

Notes

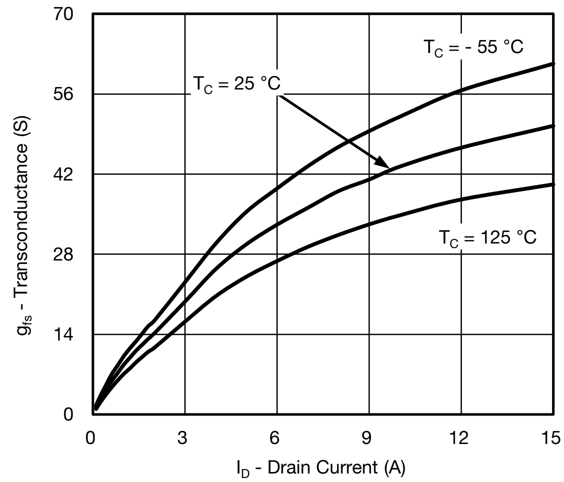
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

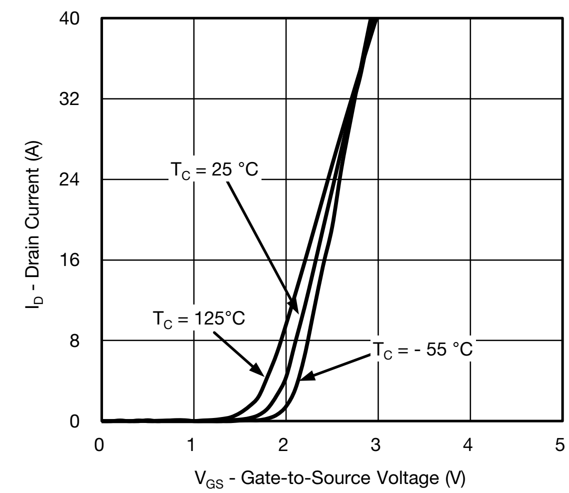
N-CHANNEL 1 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



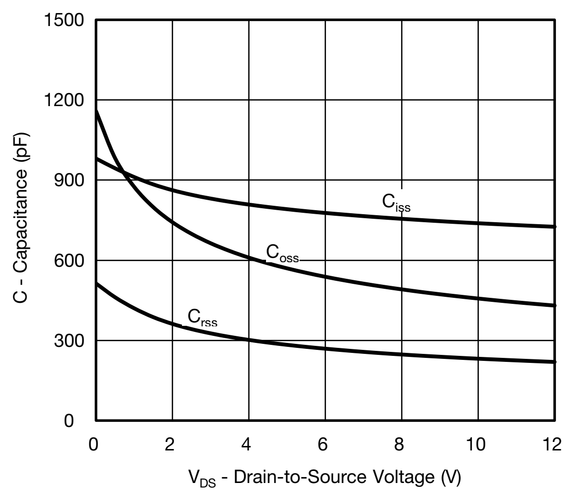
Output Characteristics



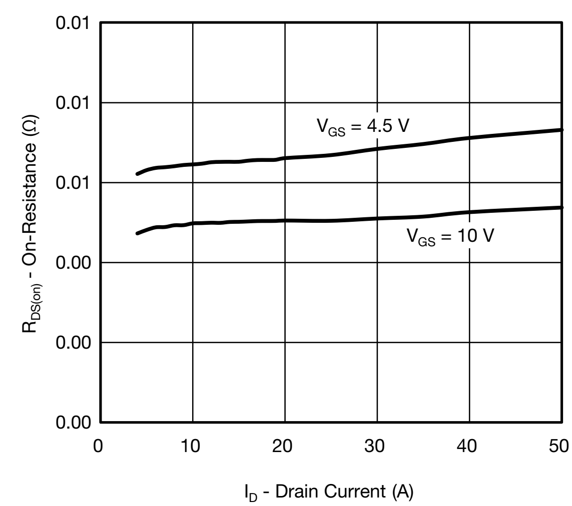
Transconductance



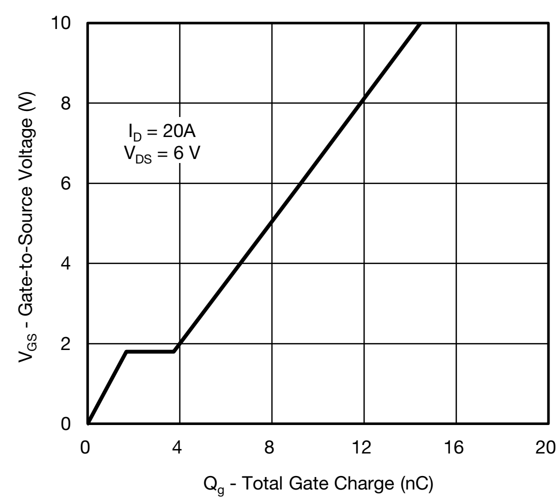
Transfer Characteristics



Capacitance

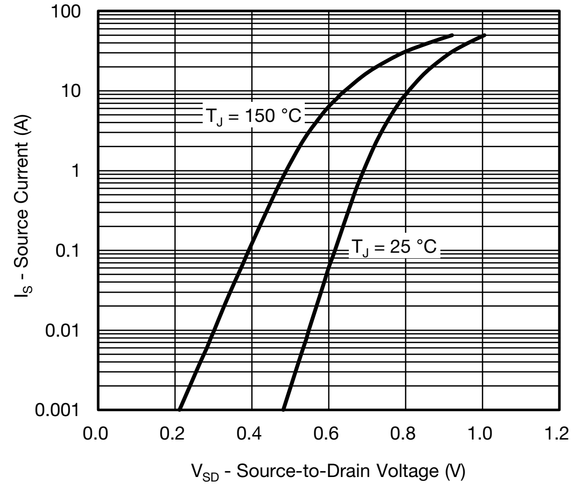


On-Resistance vs. Drain Current

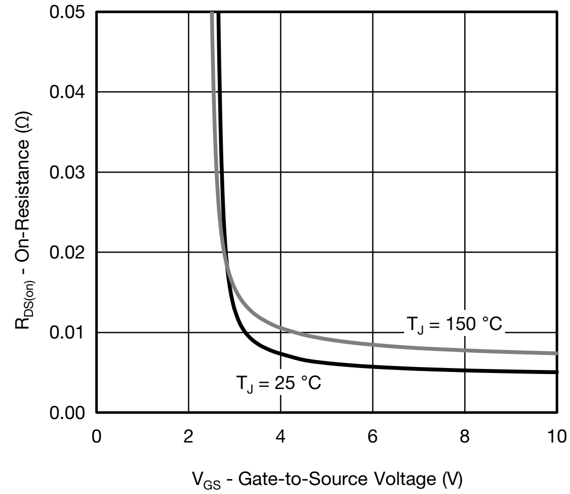


Gate Charge

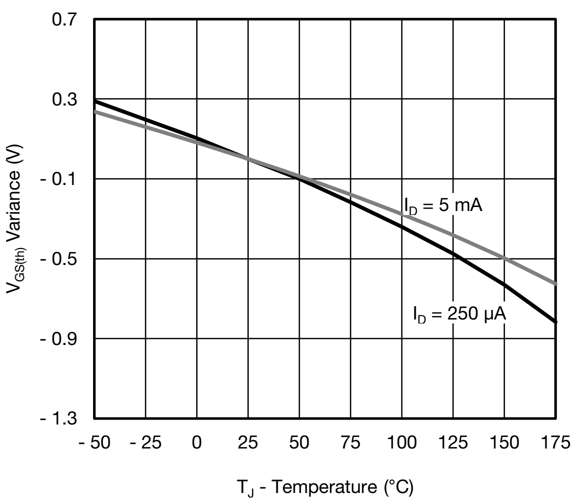
N-CHANNEL 1 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



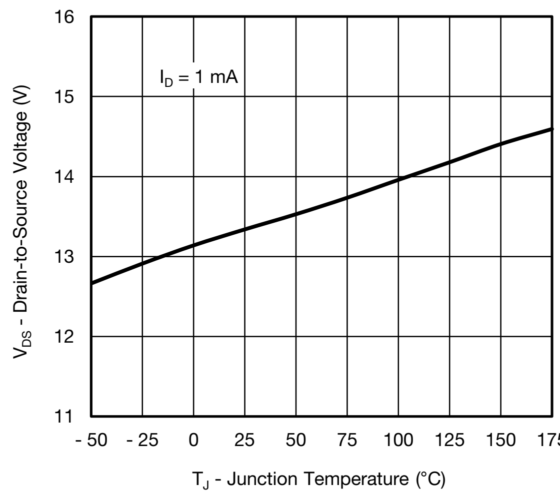
Source Drain Diode Forward Voltage



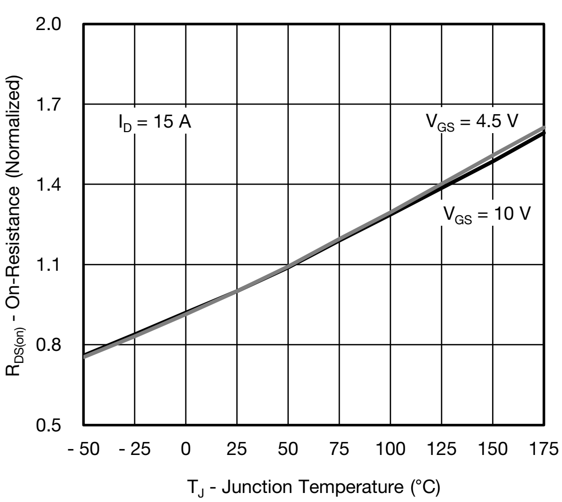
On-Resistance vs. Gate-to-Source Voltage



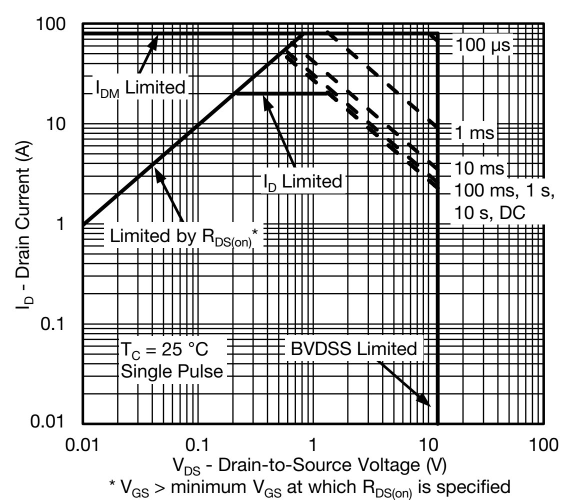
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

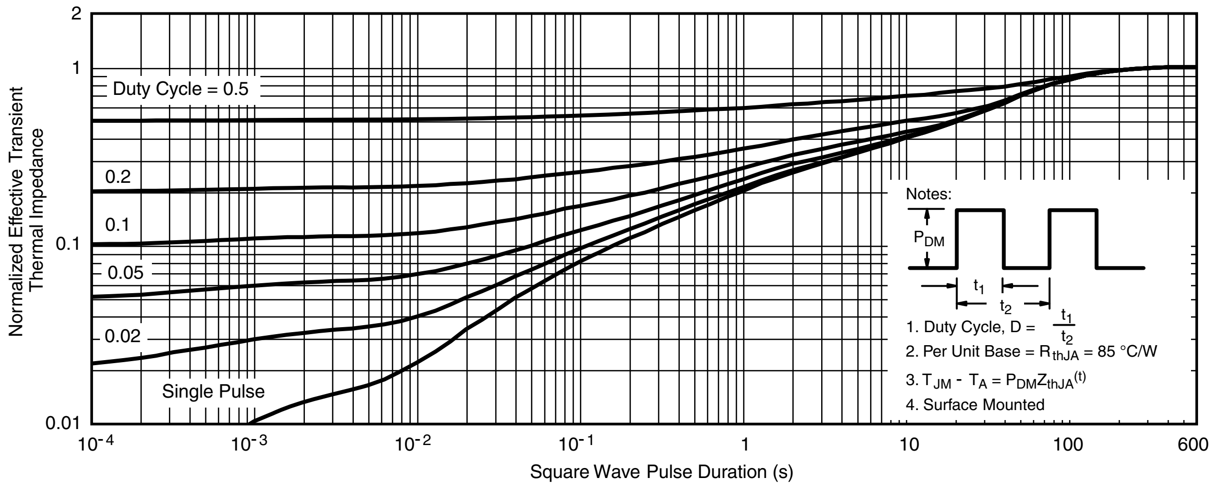


On-Resistance vs. Junction Temperature

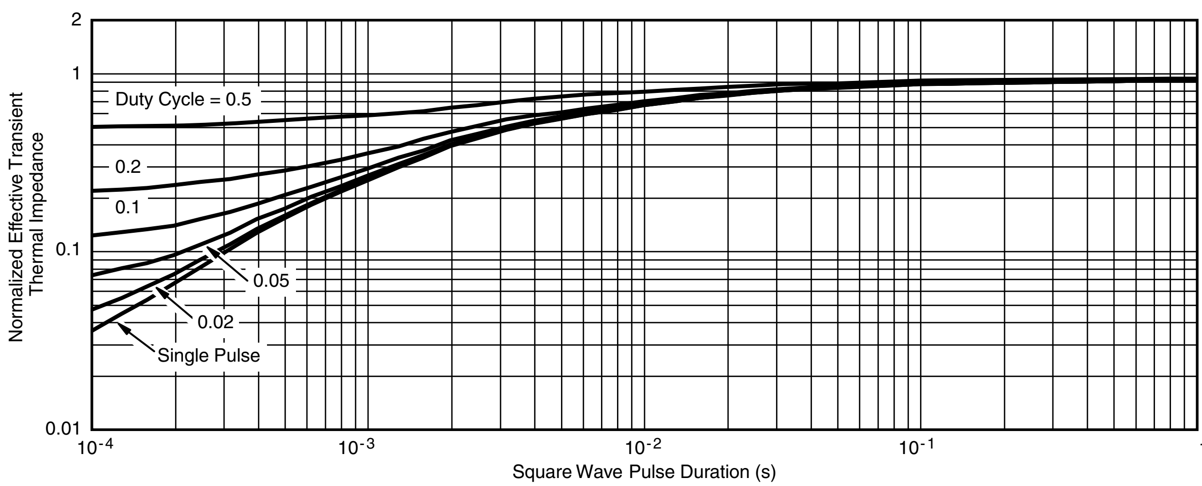


Safe Operating Area

N-CHANNEL 1 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



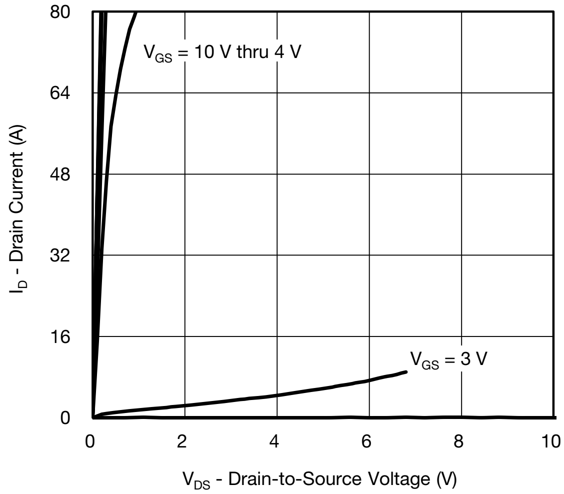
Normalized Thermal Transient Impedance, Junction-to-Case

Note

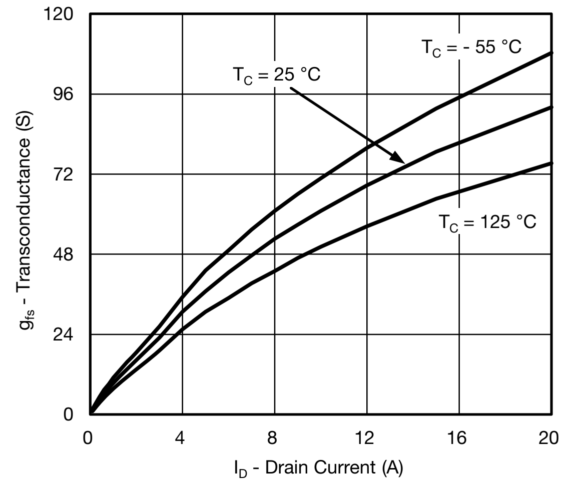
- The characteristics shown in the graph:
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

  is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

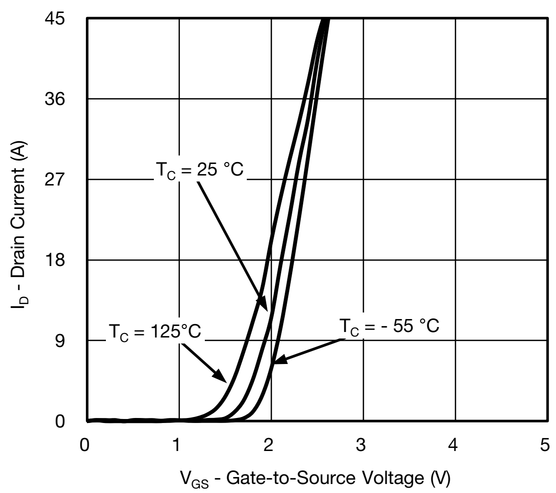
N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



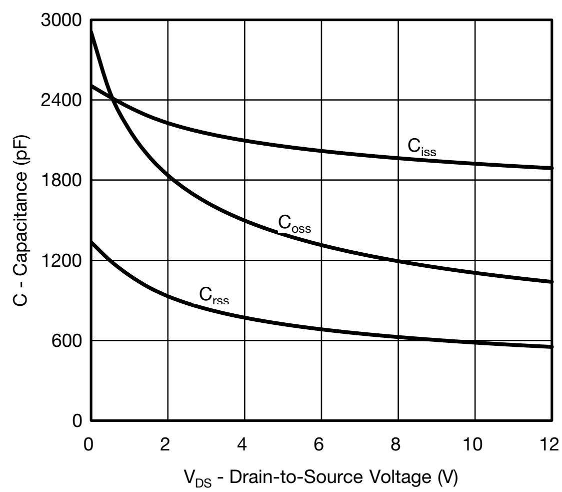
Output Characteristics



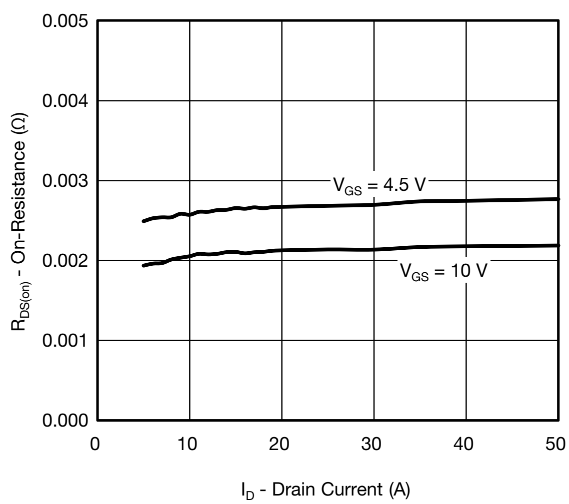
Transconductance



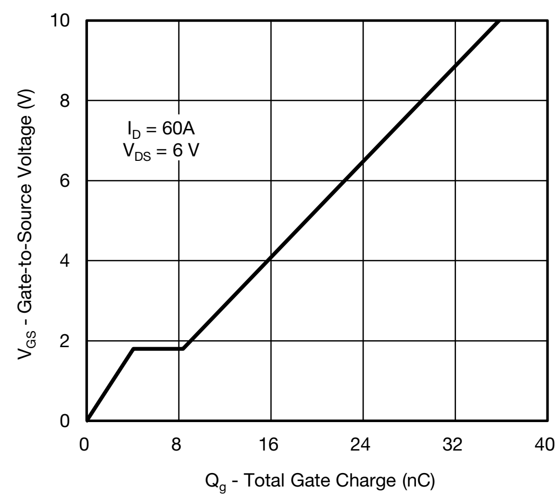
Transfer Characteristics



Capacitance

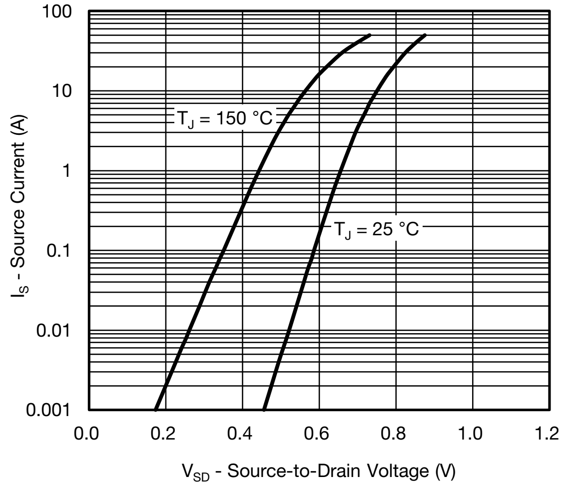


On-Resistance vs. Drain Current

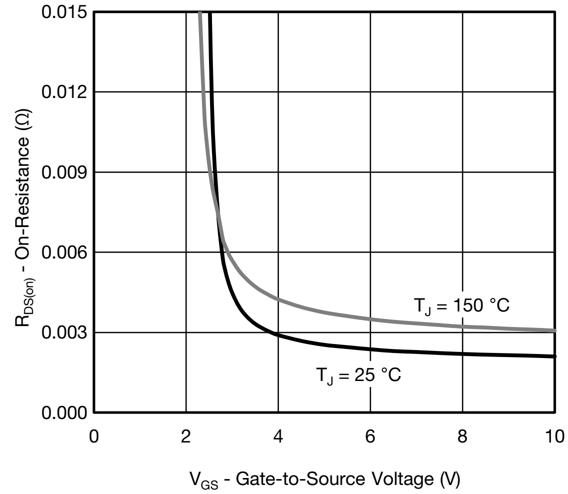


Gate Charge

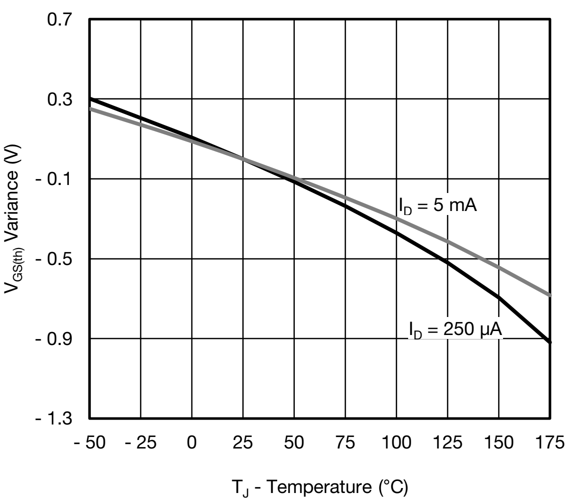
N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



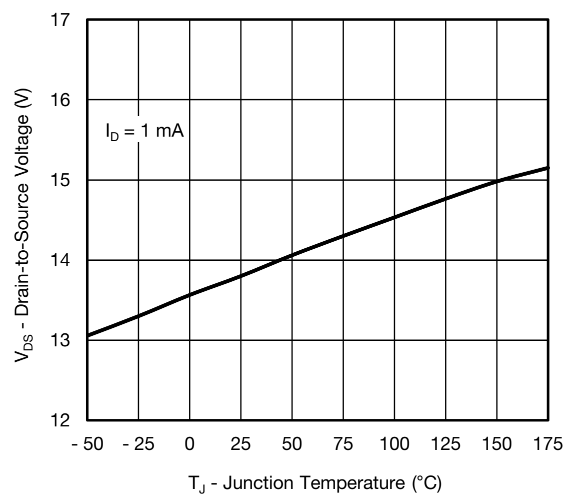
Source Drain Diode Forward Voltage



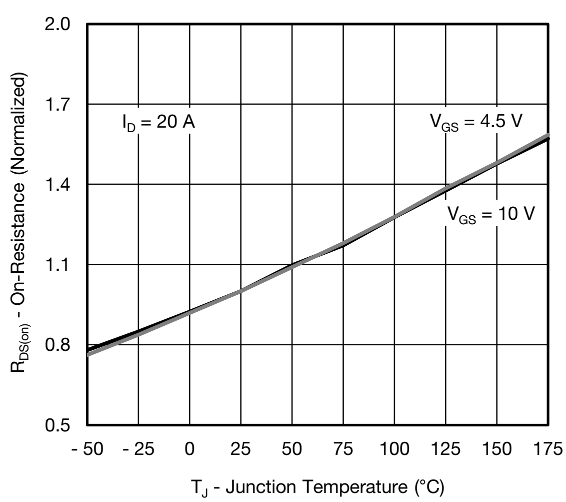
On-Resistance vs. Gate-to-Source Voltage



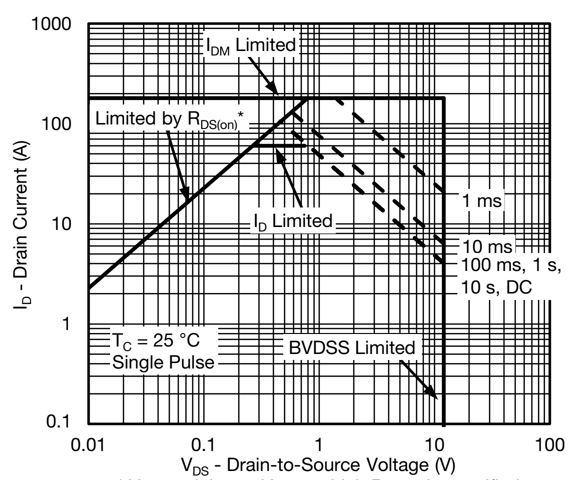
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



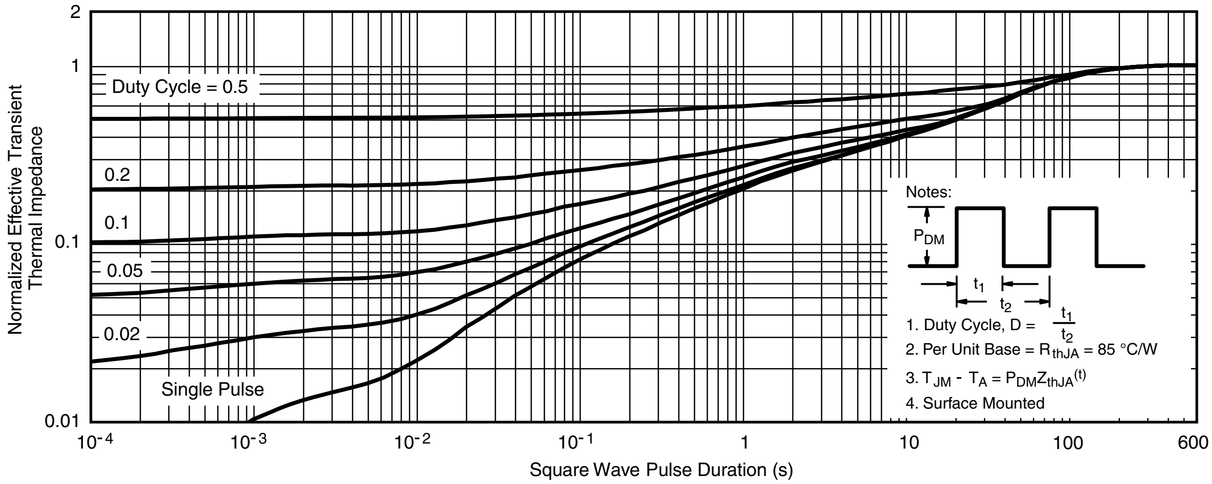
On-Resistance vs. Junction Temperature



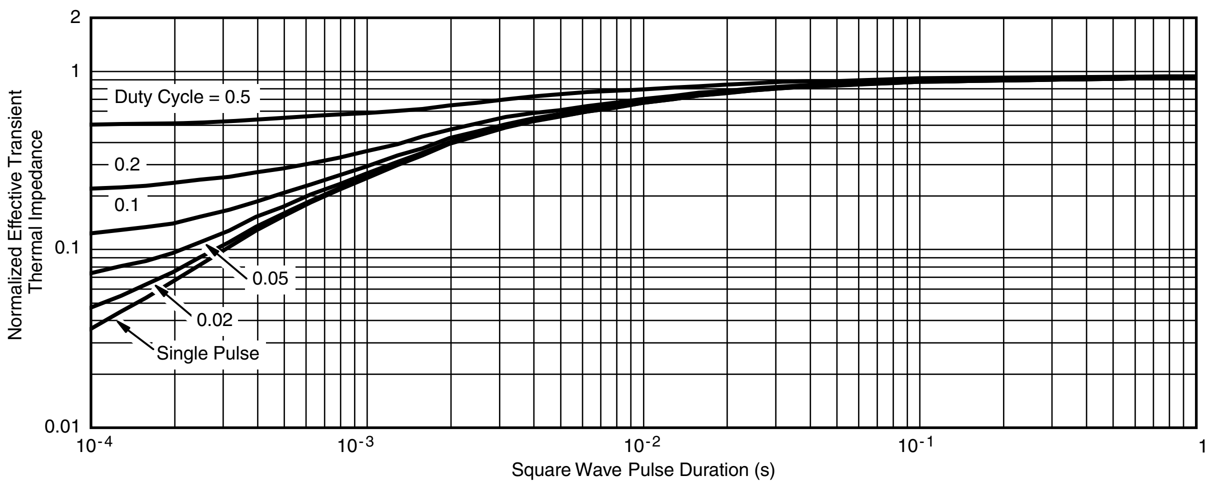
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

N-CHANNEL 2 TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the graph:
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62926.

PowerPAK® SO-8L

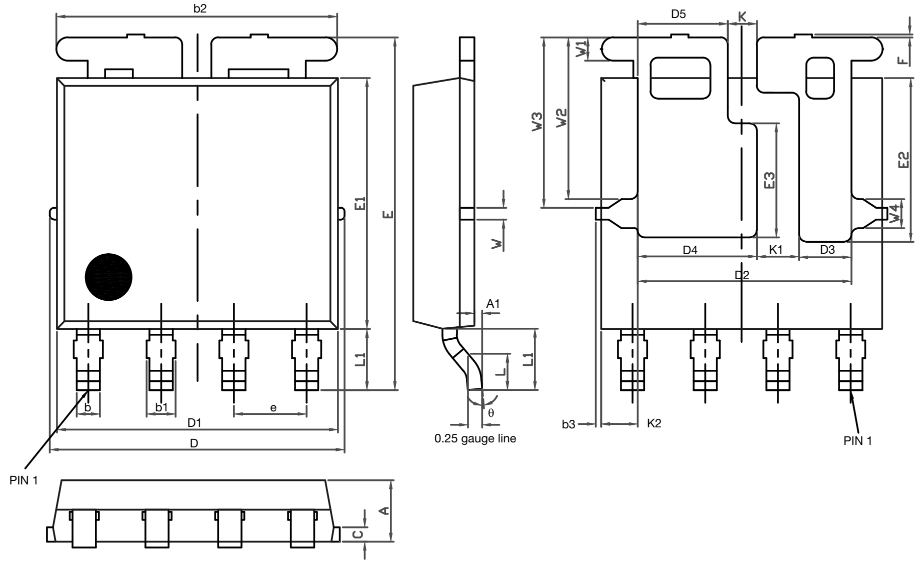
Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

DATASHEET PART NUMBER	OLD ORDERING CODE [a]	NEW ORDERING CODE
SQJ200EP	-	**SQJ200EP-T1_GE3**
SQJ202EP	-	**SQJ202EP-T1_GE3**
SQJ401EP	SQJ401EP-T1-GE3	**SQJ401EP-T1_GE3**
SQJ402EP	SQJ402EP-T1-GE3	**SQJ402EP-T1_GE3**
SQJ403EEP	SQJ403EEP-T1-GE3	**SQJ403EEP-T1_GE3**
SQJ403EP	-	**SQJ403EP-T1_GE3**
SQJ410EP	SQJ410EP-T1-GE3	**SQJ410EP-T1_GE3**
SQJ412EP	SQJ412EP-T1-GE3	**SQJ412EP-T1_GE3**
SQJ416EP	-	**SQJ416EP-T1_GE3**
SQJ418EP	-	**SQJ418EP-T1_GE3**
SQJ422EP	SQJ422EP-T1-GE3	**SQJ422EP-T1_GE3**
SQJ423EP	-	**SQJ423EP-T1_GE3**
SQJ431EP	SQJ431EP-T1-GE3	**SQJ431EP-T1_GE3**
SQJ443EP	SQJ443EP-T1-GE3	**SQJ443EP-T1_GE3**
SQJ444EP	-	**SQJ444EP-T1_GE3**
SQJ446EP	-	**SQJ446EP-T1_GE3**
SQJ456EP	SQJ456EP-T1-GE3	**SQJ456EP-T1_GE3**
SQJ457EP	-	**SQJ457EP-T1_GE3**
SQJ459EP	-	**SQJ459EP-T1_GE3**
SQJ460AEP	-	**SQJ460AEP-T1_GE3**
SQJ461EP	SQJ461EP-T1-GE3	**SQJ461EP-T1_GE3**
SQJ463EP	SQJ463EP-T1-GE3	**SQJ463EP-T1_GE3**
SQJ465EP	SQJ465EP-T1-GE3	**SQJ465EP-T1_GE3**
SQJ469EP	SQJ469EP-T1-GE3	**SQJ469EP-T1_GE3**
SQJ474EP	-	**SQJ474EP-T1_GE3**
SQJ476EP	-	**SQJ476EP-T1_GE3**
SQJ479EP	-	**SQJ479EP-T1_GE3**
SQJ486EP	SQJ486EP-T1-GE3	**SQJ486EP-T1_GE3**
SQJ488EP	SQJ488EP-T1-GE3	**SQJ488EP-T1_GE3**
SQJ500AEP	SQJ500AEP-T1-GE3	**SQJ500AEP-T1_GE3**
SQJ840EP	SQJ840EP-T1-GE3	**SQJ840EP-T1_GE3**
SQJ844AEP	SQJ844AEP-T1-GE3	**SQJ844AEP-T1_GE3**
SQJ850EP	SQJ850EP-T1-GE3	**SQJ850EP-T1_GE3**
SQJ858AEP	SQJ858AEP-T1-GE3	**SQJ858AEP-T1_GE3**
SQJ868EP	-	**SQJ868EP-T1_GE3**
SQJ886EP	SQJ886EP-T1-GE3	**SQJ886EP-T1_GE3**
SQJ910AEP	SQJ910AEP-T1-GE3	**SQJ910AEP-T1_GE3**
SQJ912AEP	SQJ912AEP-T1-GE3	**SQJ912AEP-T1_GE3**
SQJ940EP	SQJ940EP-T1-GE3	**SQJ940EP-T1_GE3**
SQJ942EP	SQJ942EP-T1-GE3	**SQJ942EP-T1_GE3**
SQJ951EP	SQJ951EP-T1-GE3	**SQJ951EP-T1_GE3**
SQJ952EP	-	**SQJ952EP-T1_GE3**
SQJ956EP	SQJ956EP-T1-GE3	**SQJ956EP-T1_GE3**
SQJ960EP	SQJ960EP-T1-GE3	**SQJ960EP-T1_GE3**
SQJ963EP	SQJ963EP-T1-GE3	**SQJ963EP-T1_GE3**
SQJ968EP	SQJ968EP-T1-GE3	**SQJ968EP-T1_GE3**
SQJ980AEP	SQJ980AEP-T1-GE3	**SQJ980AEP-T1_GE3**
SQJ992EP	SQJ992EP-T1-GE3	**SQJ992EP-T1_GE3**

Note

a. Old ordering code is obsolete and no longer valid for new orders

PowerPAK® SO-8L Assymetric Case Outline



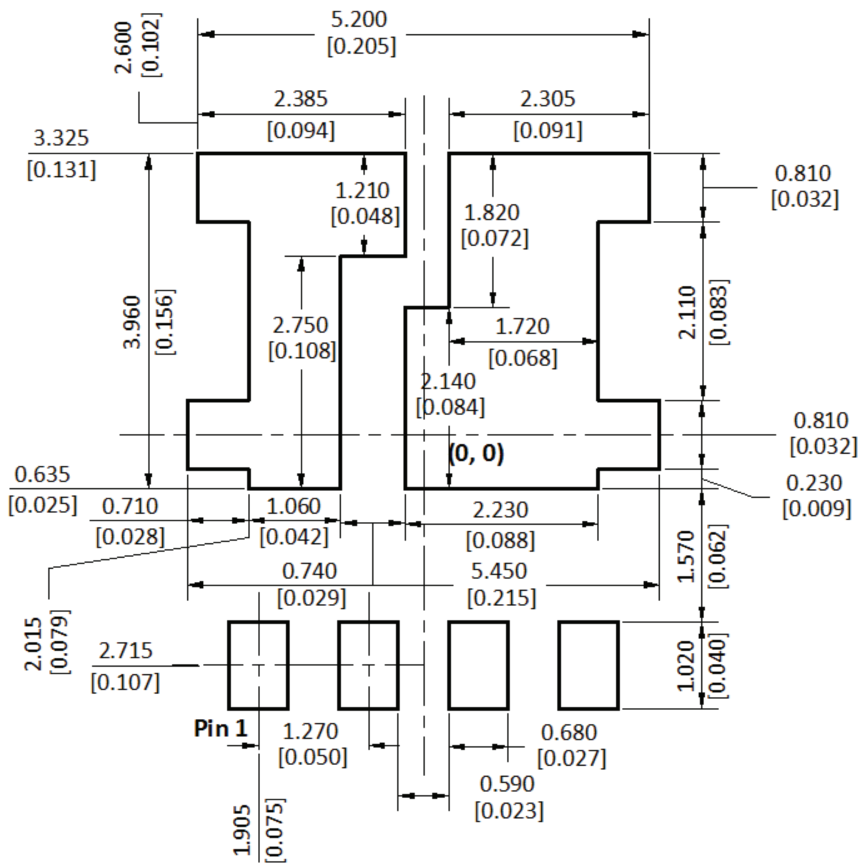
DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	0.06	0.13	0.000	0.003	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3	0.04	0.12	0.20	0.002	0.005	0.008
c	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.63	3.73	3.83	0.143	0.147	0.151
D3	0.81	0.91	1.01	0.032	0.036	0.040
D4	1.98	2.08	2.18	0.078	0.082	0.086
D5	1.47	1.57	1.67	0.058	0.062	0.066
e	1.20	1.27	1.34	0.047	0.050	0.053
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
E3	1.89	1.99	2.09	0.074	0.078	0.082
F	0.05	0.12	0.19	0.002	0.005	0.007
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K	0.41	0.51	0.61	0.016	0.020	0.024
K1	0.64	0.74	0.84	0.025	0.029	0.033
K2	0.54	0.64	0.74	0.021	0.025	0.029
W	0.13	0.23	0.33	0.005	0.009	0.013
W1	0.31	0.41	0.51	0.012	0.016	0.020
W2	2.72	2.82	2.92	0.107	0.111	0.115
W3	2.86	2.96	3.06	0.113	0.117	0.120
W4	0.41	0.51	0.61	0.016	0.020	0.024
θ	5°	10°	12°	5°	10°	12°

DWG: 6009

Note

- Millimeters will govern

RECOMMENDED MINIMUM PADs FOR PowerPAK® SO-8L DUAL ASYMMETRIC



Recommended Minimum Pads
Dimensions in mm [inches]

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